

DYNAMIC CHARACTERISTICS

APT2X101_100D60J

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	$I_F = 1A$, $di_F/dt = -100A/\mu s$, $V_R = 30V$, $T_J = 25^\circ C$	-	34		ns
t_{rr}	Reverse Recovery Time	$I_F = 100A$, $di_F/dt = -200A/\mu s$ $V_R = 400V$, $T_C = 25^\circ C$	-	180		
Q_{rr}	Reverse Recovery Charge		-	390		nC
I_{RRM}	Maximum Reverse Recovery Current		-	5	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 100A$, $di_F/dt = -200A/\mu s$ $V_R = 400V$, $T_C = 125^\circ C$	-	220		ns
Q_{rr}	Reverse Recovery Charge		-	1450		nC
I_{RRM}	Maximum Reverse Recovery Current		-	13	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 100A$, $di_F/dt = -1000A/\mu s$ $V_R = 400V$, $T_C = 125^\circ C$	-	110		ns
Q_{rr}	Reverse Recovery Charge		-	2550		nC
I_{RRM}	Maximum Reverse Recovery Current		-	40		Amps

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			.42	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			20	
W_T	Package Weight		1.03		oz
			29.2		g
Torque	Maximum Terminal & Mounting Torque			10	lb•in
				1.1	N•m

Microsemi Reserves the right to change, without notice, the specifications and information contained herein.

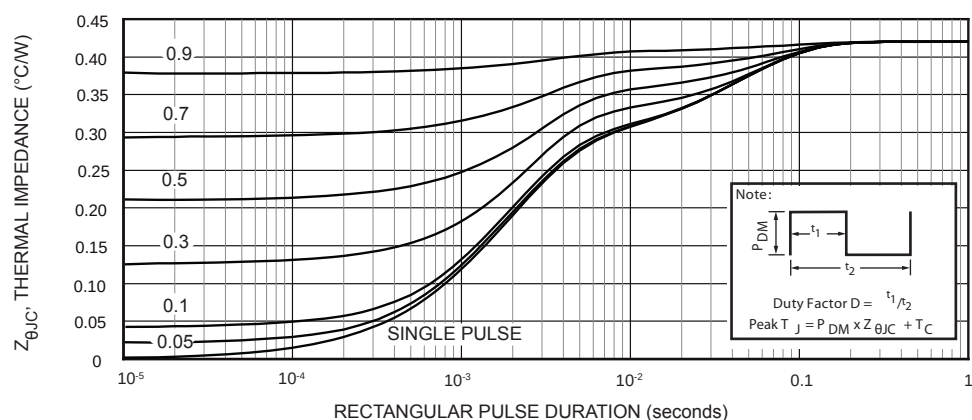


FIGURE 1. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

TYPICAL PERFORMANCE CURVES

APT2X101_100D60J

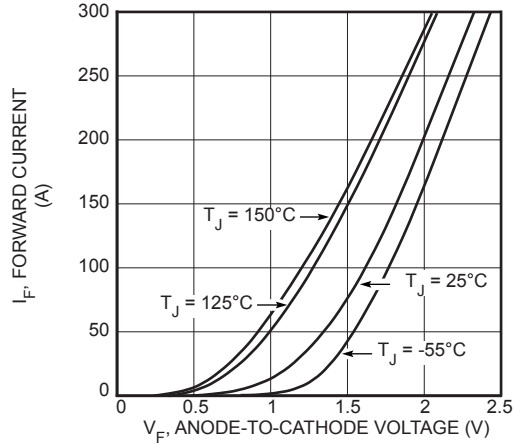


Figure 2. Forward Current vs. Forward Voltage

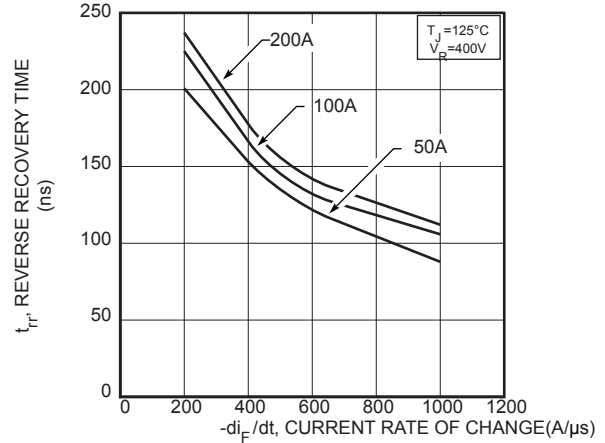


Figure 3. Reverse Recovery Time vs. Current Rate of Change

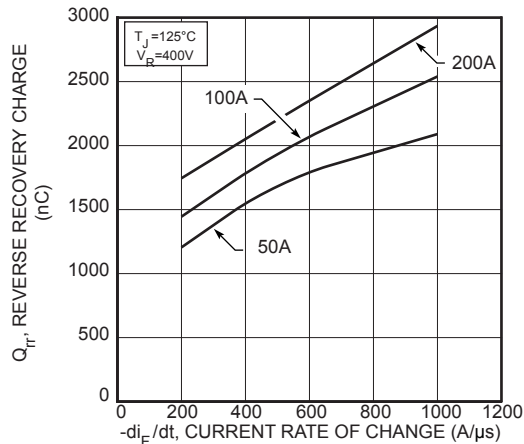


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

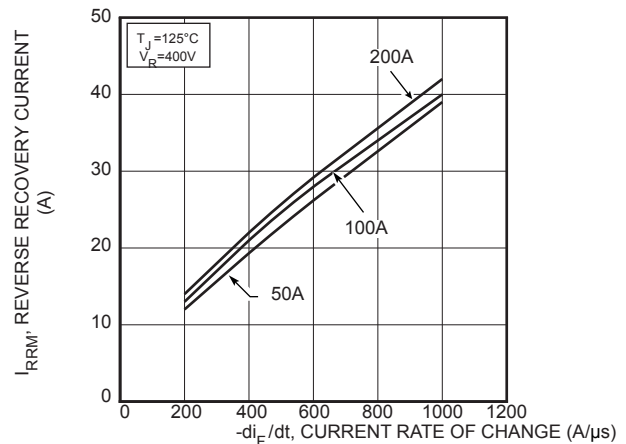


Figure 5. Reverse Recovery Current vs. Current Rate of Change

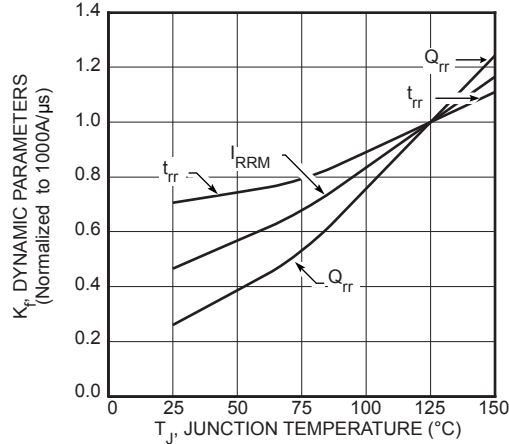


Figure 6. Dynamic Parameters vs. Junction Temperature

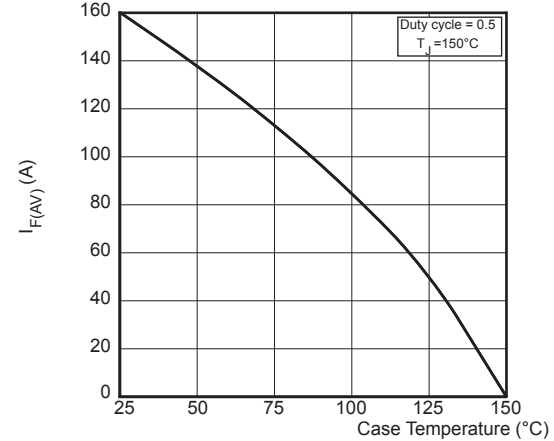


Figure 7. Maximum Average Forward Current vs. Case Temperature

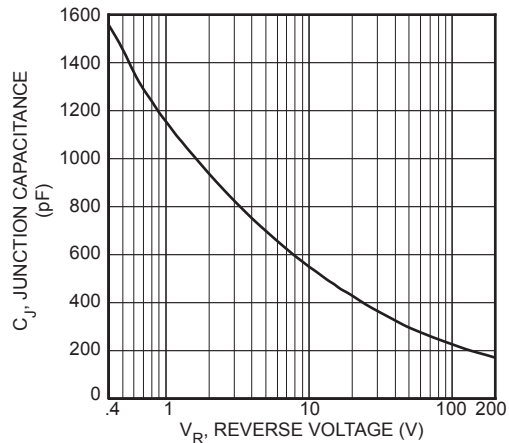


Figure 8. Junction Capacitance vs. Reverse Voltage

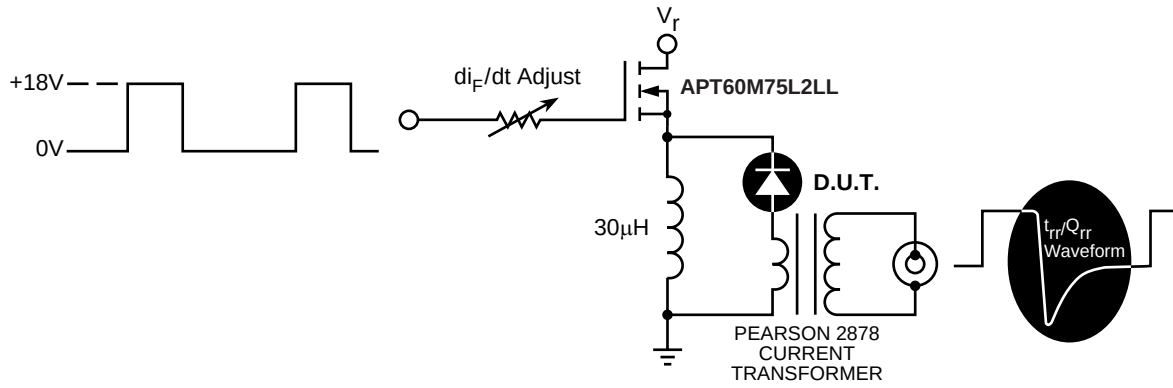


Figure 9. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current.
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

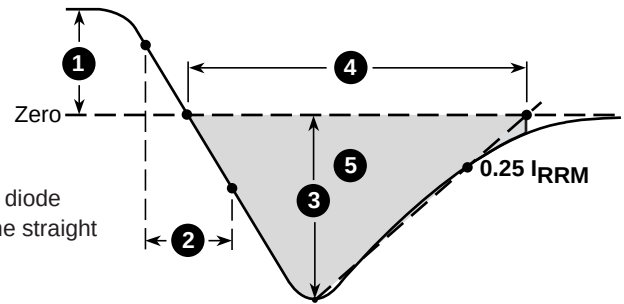


Figure 10. Diode Reverse Recovery Waveform and Definitions

SOT-227 Package Outline

